SEMICONDUCTOR

74LCXZ16245 Low Voltage 16-Bit Bidirectional Transceiver with 5V Tolerant Inputs and Outputs

General Description

The LCXZ16245 contains sixteen non-inverting bidirectional buffers with 3-STATE outputs and is intended for bus oriented applications. The device is designed for low voltage (2.7V or 3.3V) V_{CC} applications with capability of interfacing to a 5V signal environment. The device is byte controlled. Each byte has separate control inputs which could be shorted together for full 16-bit operation. The T/\overline{R} inputs determine the direction of data flow through the device. The \overline{OE} inputs disable both the A and B ports by placing them in a high impedance state.

When V_{CC} is between 0V and 1.5V, the LCXZ16245 is on the high impedance state during power-up or power-down. This places the outputs in the high impedance (Z) state preventing intermittent low impedance loading or glitching in bus oriented applications.

The LCXZ16245 is fabricated with an advanced CMOS technology to achieve high speed operation while maintaining CMOS low power dissipation.

Features

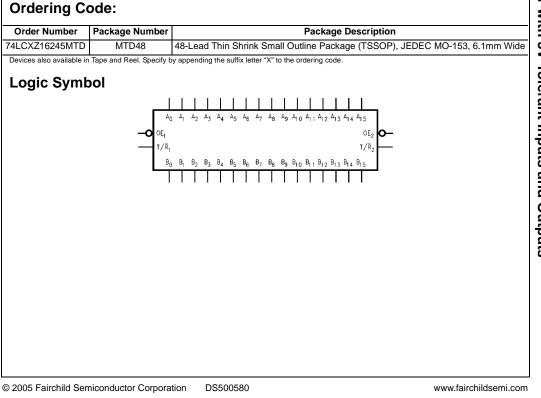
- 5V tolerant inputs and outputs
- 2.7V–3.6V V_{CC} specifications provided
- 4.5 ns t_{PD} max (V_{CC} = 3.3V), 20 µA I_{CC} max
- Power-down high impedance inputs and outputs
- Supports live insertion/withdrawal (Note 1)
- \pm 24 mA output drive (V_{CC} = 3.0V)
- Implements patented noise/EMI reduction circuitry
- Latch-up performance conforms to the requirements of JESD78

March 2002

Revised June 2005

- ESD performance:
 - Human body model > 2000V Machine model > 200V

Note 1: To ensure the high-impedance state during power up or down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pull-up resistor: the minimum value or the resistor is determined by the current-sourcing capability of the driver.



74LCXZ16245

Connection Diagram

Pin Assignment for SSOP and TSSOP					
1					
t/R ₁ —	1 4	8 — 0E ₁			
в _о —	2 4	7 — A ₀			
в ₁ —	3 4	6 A ₁			
GND —	4 4	5 — GND			
В ₂ —	5 4	4 — A ₂			
В ₃ —	6 4	3 — A ₃			
v _{cc} —	7 4	2 — V _{CC}			
В ₄ —	8 4	1 — A ₄			
в ₅ —	9 4	0 — A ₅			
GND —	10 3	9 — GND			
в ₆ —	11 3	8 — A ₆			
в ₇ —	12 3	7 — A ₇			
в ₈ —	13 3	6 — A ₈			
в ₉ —	14 3	5 — A ₉			
GND -	15 3	4 — GND			
в ₁₀ —	16 3	3 — A ₁₀			
B ₁₁ —	17 3	2 — A ₁₁			
v _{cc} —	18 3	1 — V _{CC}			
В ₁₂ —	19 3	0 — A ₁₂			
В ₁₃ —	20 2	9 — A ₁₃			
GND —	21 2	8 — GND			
B ₁₄ —	22 2	7 — A ₁₄			
B ₁₅ —	23 2	6 — A ₁₅			
t∕R ₂ —	24 2	5 — OE ₂			

Pin Descriptions

Pin Names	Description
OEn	Output Enable Input
T/R _n	Transmit/Receive Input
A ₀ -A ₁₅	Side A Inputs or 3-STATE Outputs Side B Inputs or 3-STATE Outputs
A ₀ –A ₁₅ B ₀ –B ₁₅	Side B Inputs or 3-STATE Outputs
NC	No Connect

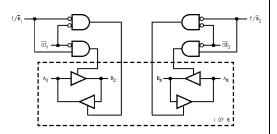
Truth Tables

In	puts	Outputo		
OE ₁	T/R ₁	- Outputs		
L	L	Bus B ₀ –B ₇ Data to Bus A ₀ –A ₇		
L	Н	Bus A ₀ –A ₇ Data to Bus B ₀ –B ₇		
Н	Х	HIGH Z State on A ₀ -A ₇ , B ₀ -B ₇		
Inp	outs	Outpute		
OE ₂	T/R ₂	Outputs		
1	1			

L	L	Bus B ₈ –B ₁₅ Data to Bus A ₈ –A ₁₅
L		Bus A ₈ –A ₁₅ Data to Bus B ₈ –B ₁₅
н	х	HIGH Z State on A ₈ -A ₁₅ , B ₈ -B ₁₅

H = HIGH Voltage Level L = LOW Voltage Level X = Immaterial Z = High Impedance

Logic Diagram



www.fairchildsemi.com

2

Symbol	Parameter	Value	Conditions	Units	
/ _{cc}	Supply Voltage	-0.5 to +7.0		V	
/1	DC Input Voltage	-0.5 to +7.0		V	
Vo	DC Output Voltage	-0.5 to +7.0	Output in 3-STATE	V	
		–0.5 to V _{CC} + 0.5	Output in HIGH or LOW State (Note 3)	te 3)	
IK	DC Input Diode Current	-50	V _I < GND	mA	
ЭК	DC Output Diode Current	-50	V _O < GND	m۸	
		+50	$V_{O} > V_{CC}$	mA	
0	DC Output Source/Sink Current	±50		mA	
CC	DC Supply Current per Supply Pin	±100		mA	
GND	DC Ground Current per Ground Pin	±100		mA	
STG	Storage Temperature	-65 to +150		°C	

Recommended Operating Conditions (Note 4)

Symbol	Parameter			Max	Units
V _{CC}	Supply Voltage	Operating	2.7	3.6	V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage	HIGH or LOW State	0	V _{CC}	V
		3-STATE	0	5.5	v
I _{OH} /I _{OL}	Output Current	V _{CC} = 3.0V - 3.6V		±24	m (
		V _{CC} = 3.0V - 3.6V V _{CC} = 2.7V - 3.0V		±12	mA
T _A	Free-Air Operating Temperature		-40	85	°C
$\Delta t / \Delta V$	Input Edge Rate, V _{IN} = 0.8V–2.0V, V _{CC} = 3.0V		0	10	ns/V

Note 2: The Absolute Maximum Ratings are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the Electrical Characteristics tables are not guaranteed at the Absolute Maximum Ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Note 3: I_O Absolute Maximum Rating must be observed.

Note 4: Unused inputs or I/O's must be held HIGH or LOW. They may not float.

DC Electrical Characteristics

Symbol	Parameter	Conditions	V _{cc}	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		Units
Symbol		Conditions	(V)	Min	Max	Units
VIH	HIGH Level Input Voltage		2.7 - 3.6	2.0		V
VIL	LOW Level Input Voltage		2.7 - 3.6		0.8	V
V _{OH}	HIGH Level Output Voltage	I _{OH} = -100 μA	2.7 - 3.6	V _{CC} - 0.2		
		$I_{OH} = -12 \text{ mA}$	2.7	2.2		v
		I _{OH} = -18 mA	3.0	2.4		v
		I _{OH} = -24 mA	3.0	2.2		
V _{OL}	LOW Level Output Voltage	I _{OL} = 100 μA	2.7 - 3.6		0.2	
		I _{OL} = 12 mA	2.7		0.4	v
		I _{OL} = 16 mA	3.0		0.4	v
		I _{OL} = 24 mA	3.0		0.55	
l _l	Input Leakage Current	$0 \le V_I \le 5.5 V$	2.7 - 3.6		±5.0	μA
I _{OZ}	3-STATE I/O Leakage	$0 \le V_0 \le 5.5V$ $V_1 = V_{1H} \text{ or } V_{1L}$	2.7 - 3.6		±5.0	μA
I _{OFF}	Power-Off Leakage Current	$V_{I} \text{ or } V_{O} = 5.5 V$	0		10	μA
I _{PU/PD}	Power-Up/Power-Down 3-STATE Output Current	$V_O = 0.5V$ to V_{CC} $V_I = V_{CC}$ or GND	0 - 1.5		±5.0	μA
ICC	Quiescent Supply Current	V _I = V _{CC} or GND	2.7–3.6		225	<u> </u>
		$3.6V \leq V_I, \ V_O \leq 5.5V \ (Note \ 5)$	2.7–3.6		±225	μA
Δl _{CC}	Increase in I _{CC} per Input	$V_{IH} = V_{CC} - 0.6V$	2.7-3.6		500	μA

3

74LCXZ16245

AC Electrical Characteristics

Symbol			$T_A = -40^{\circ}C$ to $+85^{\circ}C$, $R_L = 500\Omega$				
	Parameter	$\textbf{V}_{\textbf{CC}} = \textbf{3.3V} \pm \textbf{0.3V}$		V _{CC}	V _{CC} = 2.7V C _L = 50 pF		
		C _L =	C _L = 50 pF				
		Min	Max	Min	Max		
PHL	Propagation Delay	1.0	4.5	1.0	5.2	ns	
PLH	A _n to B _n or B _n to A _n	1.0	4.5	1.0	5.2	115	
PZL	Output Enable Time	1.0	6.5	1.0	7.2	ns	
^I PZH		1.0	6.5	1.0	7.2	115	
PLZ	Output Disable Time	1.0	6.4	1.0	6.9	ns	
PHZ		1.0	6.4	1.0	6.9	115	
OSHL	Output to Output Skew (Note 6)		1.0			ns	
t _{OSLH}			1.0			ns	

Note 6: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}). Parameter guaranteed by design.

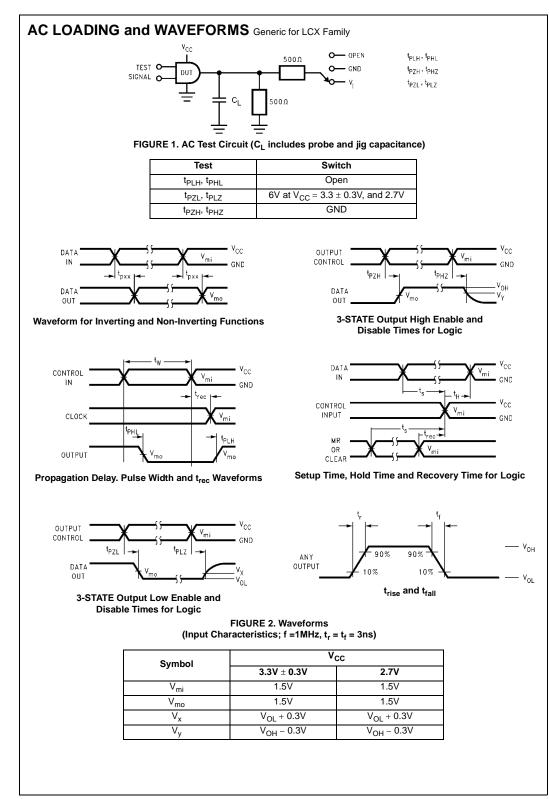
Dynamic Switching Characteristics

Symbol	Parameter	Conditions	V _{cc}	$T_A = 25^{\circ}C$	Units
			(V)	Typical	onno
V _{OLP}	Quiet Output Dynamic Peak V _{OL}	$C_{L} = 50 \text{ pF}, V_{IH} = 3.3 \text{V}, V_{IL} = 0 \text{V}$	3.3	0.8	V
V _{OLV}	Quiet Output Dynamic Valley V _{OL}	$C_L = 50 \text{ pF}, \text{ V}_{IH} = 3.3 \text{ V}, \text{ V}_{IL} = 0 \text{ V}$	3.3	-0.8	V

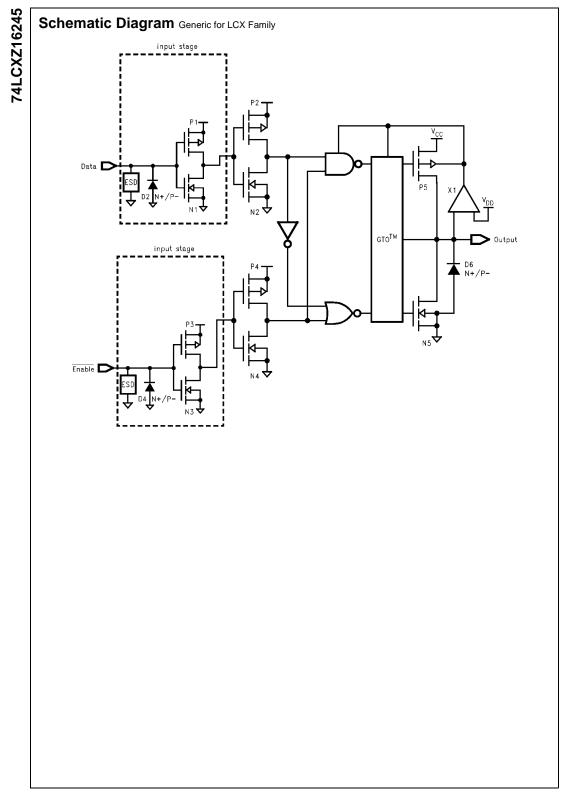
Capacitance

Symbol	Parameter Conditions		Typical	Units
CIN	Input Capacitance	$V_{CC} = Open, V_I = 0V \text{ or } V_{CC}$	7	pF
C _{I/O}	Input/Output Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC} , $f = 10$ MHz	20	pF

www.fairchildsemi.com



www.fairchildsemi.com



www.fairchildsemi.com

6

